N-Channel Super Junction Power MOSFET Ⅳ

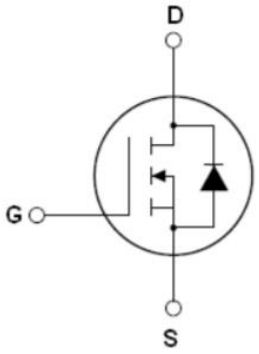
General Description

The series of devices use advanced trench gate super junction technology and design to provide ultra-low $R_{DS(ON)}$ and low gate charge and With a rapid recovery body diode.This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, industrial power applications,Fast charger, new energy vehicle charging pile, on-board OBC etc.

$V_{DS\ min@Tjmax}$	650	V
$R_{DS(ON)TYP.}$	1950	mΩ
I_D	1.8	A
Qg	3.9	nC

Features

- New technology for high voltage device
- Ultra low on-resistance and ultra low conduction losses
- Ultra Low Gate Charge cause lower driving requirements
- Diode reverse recovery speed is super fast
- 100% Avalanche Tested and 100% T_{rr} Tested
- High reliability
- ROHS compliant



Schematic diagram

Application

- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）
- On-board charger(OBC)

Package Marking And Ordering Information

Device	Device Package	Marking
NCE60N2K1I	TO-251	NCE60N2K1I

TO-251

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V）	V_{DS}	600	V
Gate-Source Voltage (V_{DS}=0V) ,AC (f>1 Hz)	V_{GS}	±30	V
Gate-Source Voltage (V_{DS}=0V) ,DC	V_{GS}	±20	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	1.8	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	1.26	A
Pulsed drain current (Note 1)	$I_{DM\ (pluse)}$	5.4	A
Maximum Power Dissipation(Tc=25℃) Derate above 25°C	P_D	19 0.13	W W/°C
Single pulse avalanche energy (Note 2)	E_{AS}	1.25	mJ
Single pulse avalanche current (Note 2)	I_{AS}	0.5	A
Repetitive Avalanche energy ， t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.02	mJ

Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	15	V/ns
Drain Source voltage slope， V_{DS} ≤480 V	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+175	°C

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	7.9	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250uA	600			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=600V,V_{GS}=0V			1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=600V,V_{GS}=0V			100	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±200	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	2.5	3.2	4.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=0.9A		1950	2100	mΩ
Dynamic Characteristics						
Gate Resistance	Rg	F=1MHZ, D-S short		17		Ω
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1MHz		119		pF
Output Capacitance	C_{oss}			17.3		pF
Reverse Transfer Capacitance	C_{rss}			6.8		pF
Total Gate Charge	Q_g	V_{DS}=450V,I_D=0.8A, V_{GS}=10V		3.9		nC
Gate-Source Charge	Q_{gs}			0.4		nC
Gate-Drain Charge	Q_{gd}			1		nC
Gate plateau voltage	Vgp			4.9		V
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=380V,I_D=0.9A, R_G=3Ω,V_{GS}=10V		6		nS
Turn-on Rise Time	t_r			6		nS
Turn-Off Delay Time	$t_{d(off)}$			29		nS
Turn-Off Fall Time	t_f			48		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			1.8	A
Pulsed-Source-drain current(Body Diode)	I_{SDM}				5.4	A
Forward on voltage	V_{SD}	Tj=25°C,I_{SD}=1.8A,V_{GS}=0V		0.9	1.2	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F=0.9 A, di/dt=100A/μs		130		nS
Reverse Recovery Charge	Q_{rr}			0.52		uC
Peak reverse recovery current	I_{rrm}			8		A

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

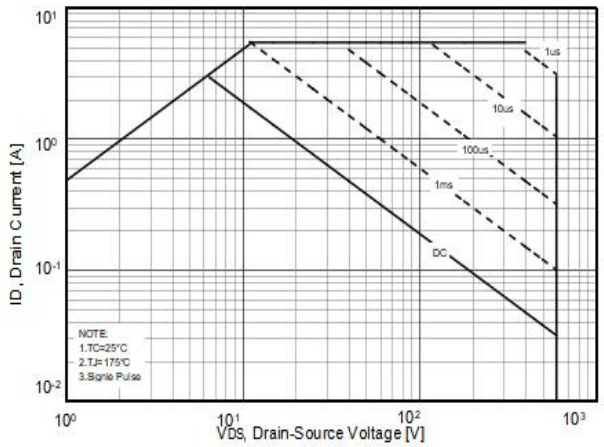


Figure2. Capacitance

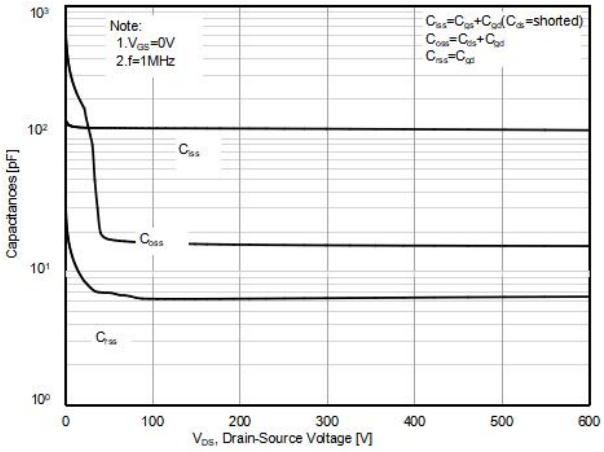


Figure3. Source-Drain Diode Forward Voltage

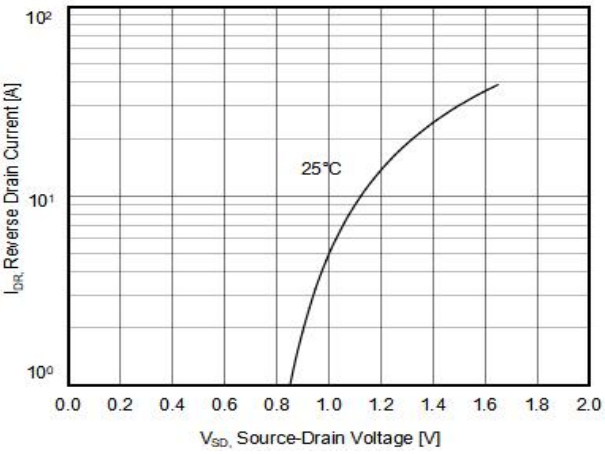


Figure4. Output characteristics

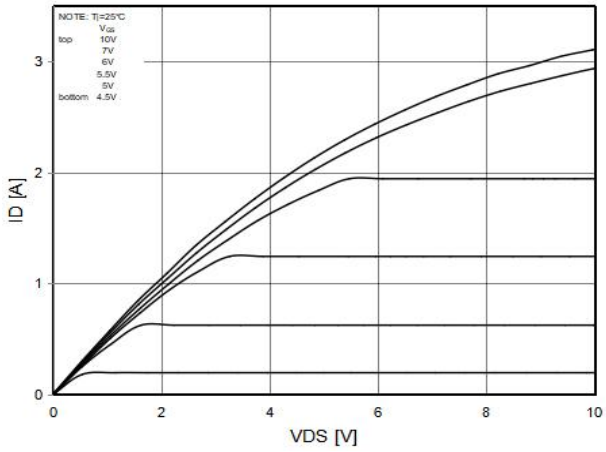


Figure5. Transfer characteristics

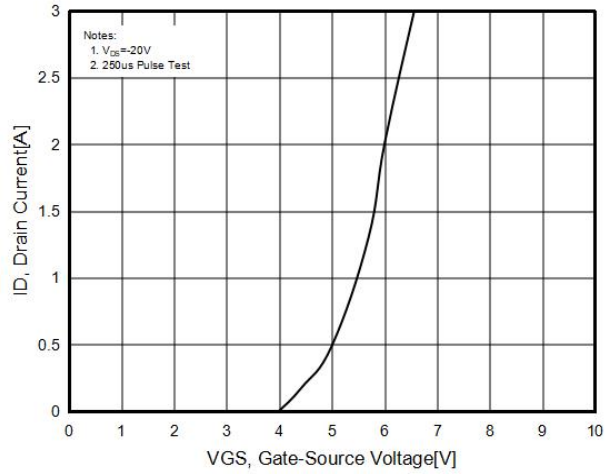


Figure6. Static drain-source on resistance

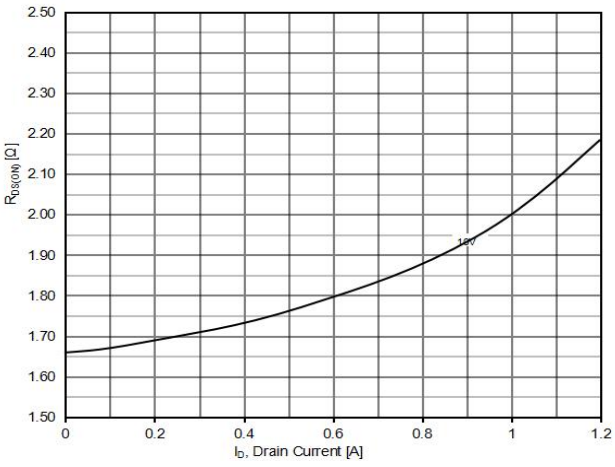


Figure7. $R_{DS(ON)}$ vs Junction Temperature

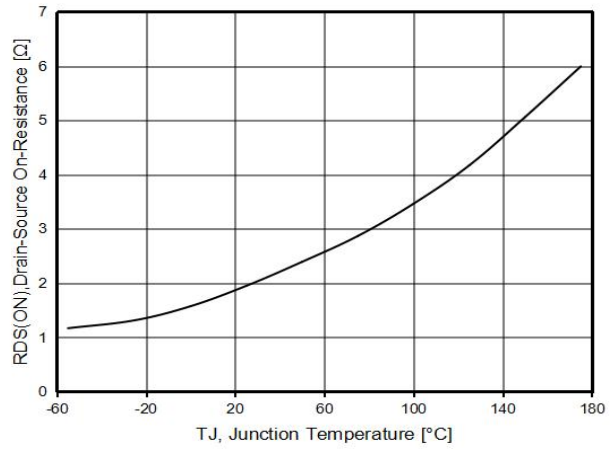


Figure8. BV_{DSS} vs Junction Temperature

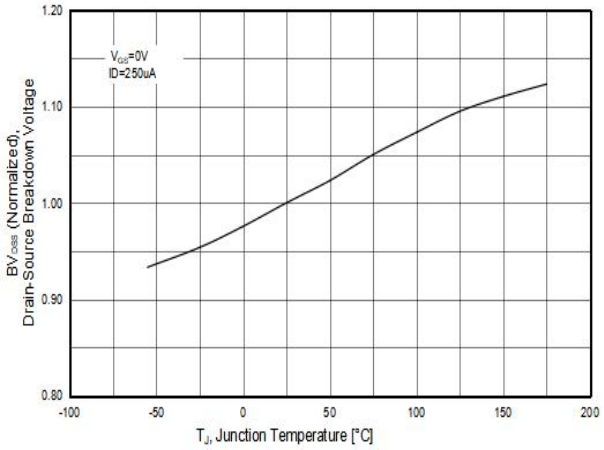


Figure9. Maximum I_D vs Junction Temperature

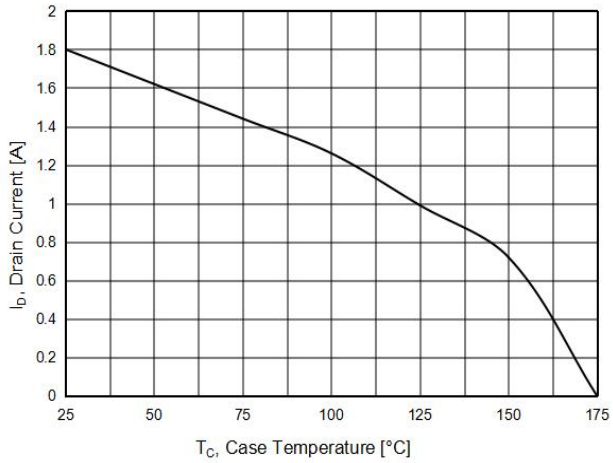
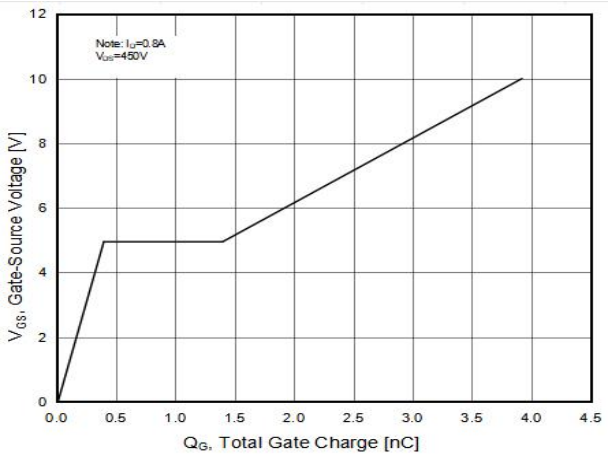
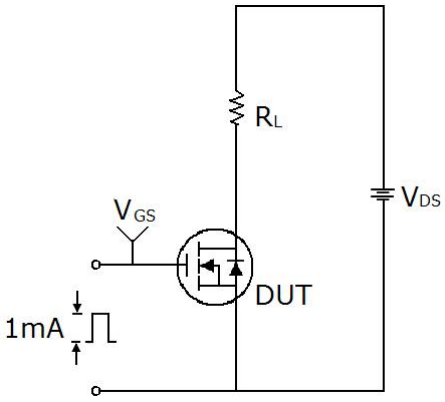


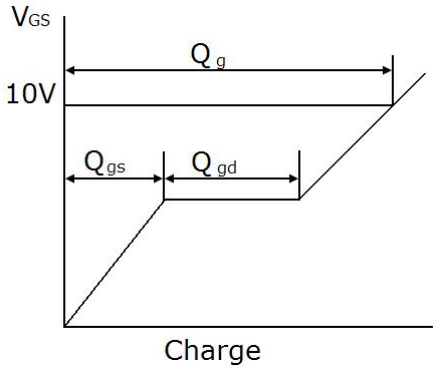
Figure10. Gate charge waveforms



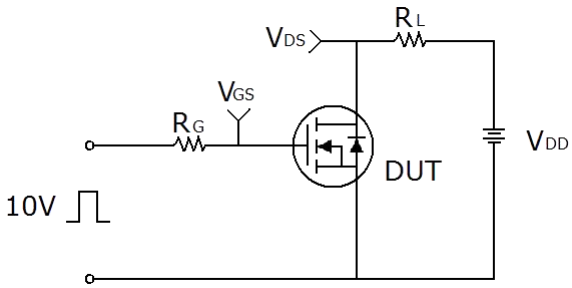
Test circuit

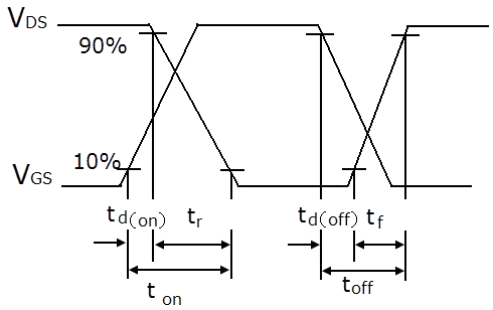
1）Gate charge test circuit & Waveform



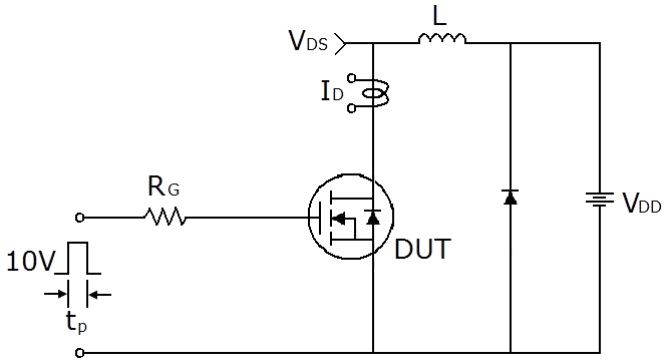


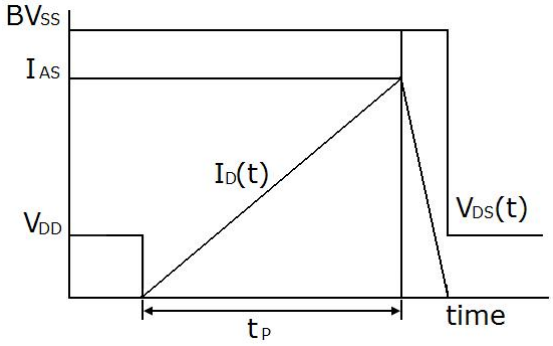
2）Switch Time Test Circuit：



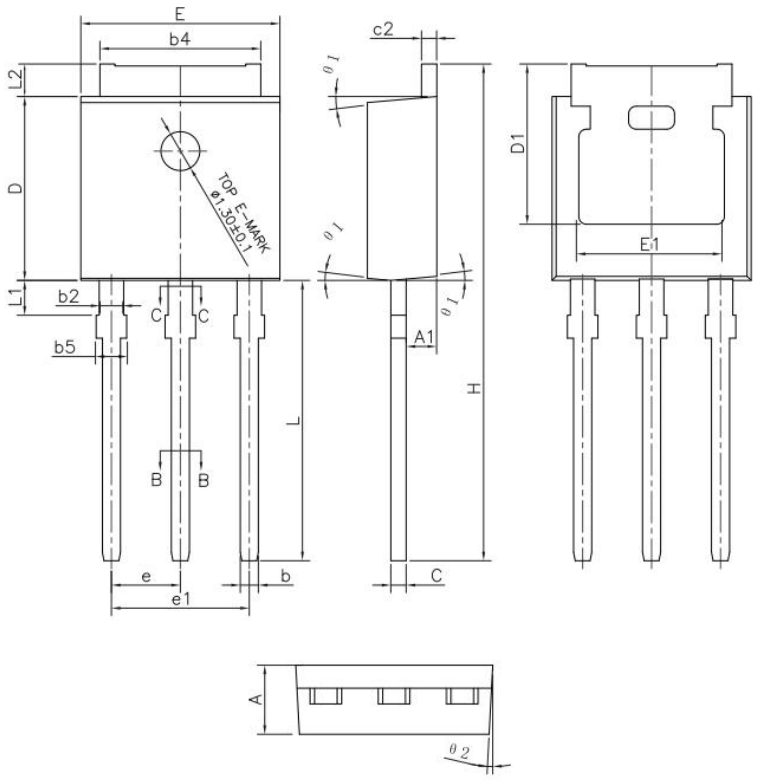


3）Unclamped Inductive Switching Test Circuit & Waveforms



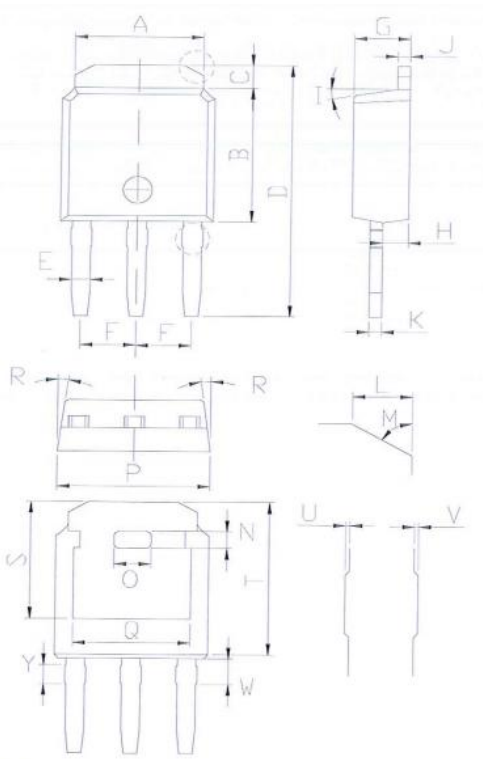


TO-251-P Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.35	0.087	0.093
A1	0.90	1.10	0.035	0.043
b	0.56	0.69	0.022	0.027
b1	0.55	0.65	0.022	0.026
b2	0.77	0.90	0.030	0.035
b3	0.76	0.86	0.030	0.034
b4	5.23	5.43	0.206	0.214
c	0.46	0.59	0.018	0.023
c1	0.45	0.55	0.018	0.022
c2	0.46	0.59	0.018	0.023
D	6.00	6.20	0.236	0.244
D1	5.20	-	0.205	-
E	6.50	6.70	0.256	0.264
E1	4.60	5.00	0.181	0.197
e	2.24	2.34	0.088	0.092
e1	4.47	4.67	0.176	0.184
H	16.18	16.78	0.637	0.661
L	9.00	9.60	0.354	0.378
L1	0.95	1.35	0.037	0.053
L2	0.90	1.25	0.035	0.049

TO-251-L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	5.04	5.64	0.198	0.222
B	5.70	6.30	0.224	0.248
C	0.75	1.35	0.030	0.053
D	11.01	11.61	0.433	0.457
E	0.61	0.91	0.024	0.036
F	2.13	2.43	0.084	0.096
G	2.00	2.60	0.079	0.102
H	0.76	1.36	0.030	0.054
J	0.36	0.66	0.014	0.026
K	0.37	0.67	0.015	0.026
L	0.50	1.10	0.020	0.043
N	0.45	1.05	0.018	0.041
O	1.50	2.10	0.059	0.083
P	6.30	6.90	0.248	0.272
Q	4.55	5.15	0.179	0.203
S	5.00	5.60	0.197	0.220
T	6.60	7.20	0.260	0.283
W	0.90	1.40	0.035	0.055
Y	0.60	1.10	0.024	0.043

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